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ESD



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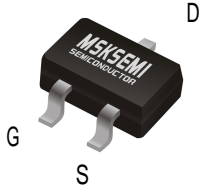


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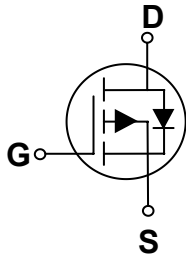
Product data sheet

Features

- -30V, -4.2A, $R_{DS(ON)} = 45m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available



SOT-23-3L



Applications

- Notebook
- Load Switch
- Battery Protection
- Hand held Instruments

BVDSS	R _{DS(ON)}	I _D
-30V	45mΩ	-4.2A

Absolute Maximum Ratings T_c=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _A =25°C)	-4.2	A
	Drain Current – Continuous (T _A =70°C)	-3.3	A
I _{DM}	Drain Current – Pulsed ¹	-16.4	A
P _D	Power Dissipation (T _A =25°C)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/ °C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	80	°C/ W

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.03	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3A	---	45	60	mΩ
		V _{GS} =-4.5V, I _D =-2A	---	60	80	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.5	-2.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-3A	---	3.5	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A	---	5.1	---	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	2	---	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	2.2	---	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =-15V, V _{GS} =-10V, R _G =6Ω I _D =-1A	---	3.4	---	ns
T _r	Rise Time ^{2, 3}		---	10.8	---	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	26.9	---	
T _f	Fall Time ^{2, 3}		---	6.9	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHz	---	560	---	pF
C _{oss}	Output Capacitance		---	55	---	
C _{rss}	Reverse Transfer Capacitance		---	40	---	

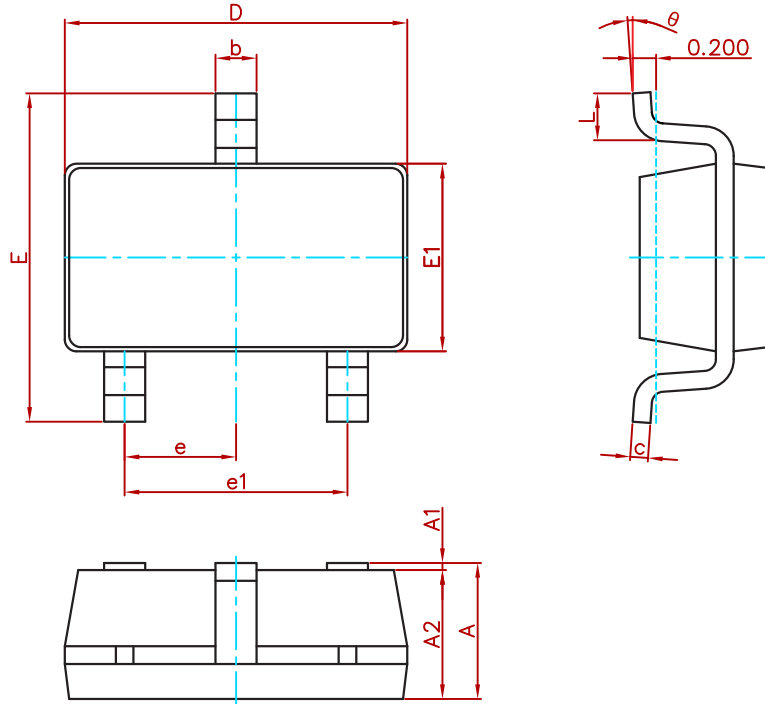
Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-4.2	A
I _{SM}	Pulsed Source Current		---	---	-16.4	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

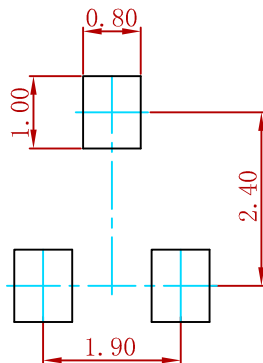
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3407A	SOT-23-3L	3000

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